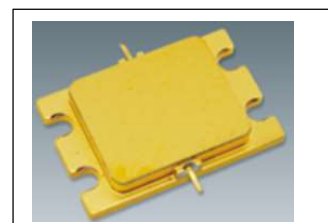


2.7-2.9GHz, 300W, 50V GaN IMFET PA

Description

The SMBV2729-300H2 is a 300-watt, single stage integrated Power Amplifier Module, designed for pulsed amplifier applications, with frequencies from 2.7 to 2.9GHz. The module is 50 Ω input/output matched and requires minimal external components.

The module implements multiple GaN active dice and its matching network within highly compact 17*24 mm metal RF package with excellent capability for heat dissipation.



● Typical Pulsed CW RF performance(100us, 10%) $V_{DS}=50V$, $V_{GS}=-3.65V$

Freq (MHz)	Power Gain (dB)	Psat (dBm)	Psat (W)	Psat Eff(%)
2700	12.36	55.45	350.62	63
2800	13.11	55.47	352.67	65
2900	12.13	55.45	350.46	65

Product Features

- Operating Frequency Range: 2.7-2.9GHz
- Operating Drain Voltage(Recommended): +50V
- 50 Ω Input/Output (External DC block capacitor needed)
- $Psat \geq 300W$ (Typical, Pulsed CW)
- Power gain @ $P_{out}=300W$: >13dB
- Efficiency: >60%
- 17*24 mm metal RF package
- Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

Applications

- S band power amplifier

Important Note: Proper Biasing Sequence for GaN HEMT Transistors

Turning the device ON

1. Set VGS to the pinch--off (VP) voltage, typically -5 V
2. Turn on VDS to nominal supply voltage (28V)
3. Increase VGS until IDS current is attained
4. Apply RF input power to desired level

Turning the device OFF

1. Turn RF power off
2. Reduce VGS down to VP, typically -5 V
3. Reduce VDS down to 0 V
4. Turn off VGS

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain--Source Voltage	V_{DS}	200	Vdc
Gate--Source Voltage	V_{GS}	-10 to +2	Vdc
Operating Voltage	V_{DD}	+55	Vdc
Storage Temperature Range	T_{stg}	-65 to +150	°C
Case Operating Temperature	T_c	+150	°C
Operating Junction Temperature	T_j	+225	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case $T_C = 25^\circ\text{C}$, $P_{out} = 300\text{W}$ Pulsed CW, FEA	$R_{\theta JC}$	0.9	$^\circ\text{C/W}$

TYPICAL CHARACTERISTICS

Figure 1. Power Gain, Efficiency as function of P_{out} under pulse conditions 100us, 10%

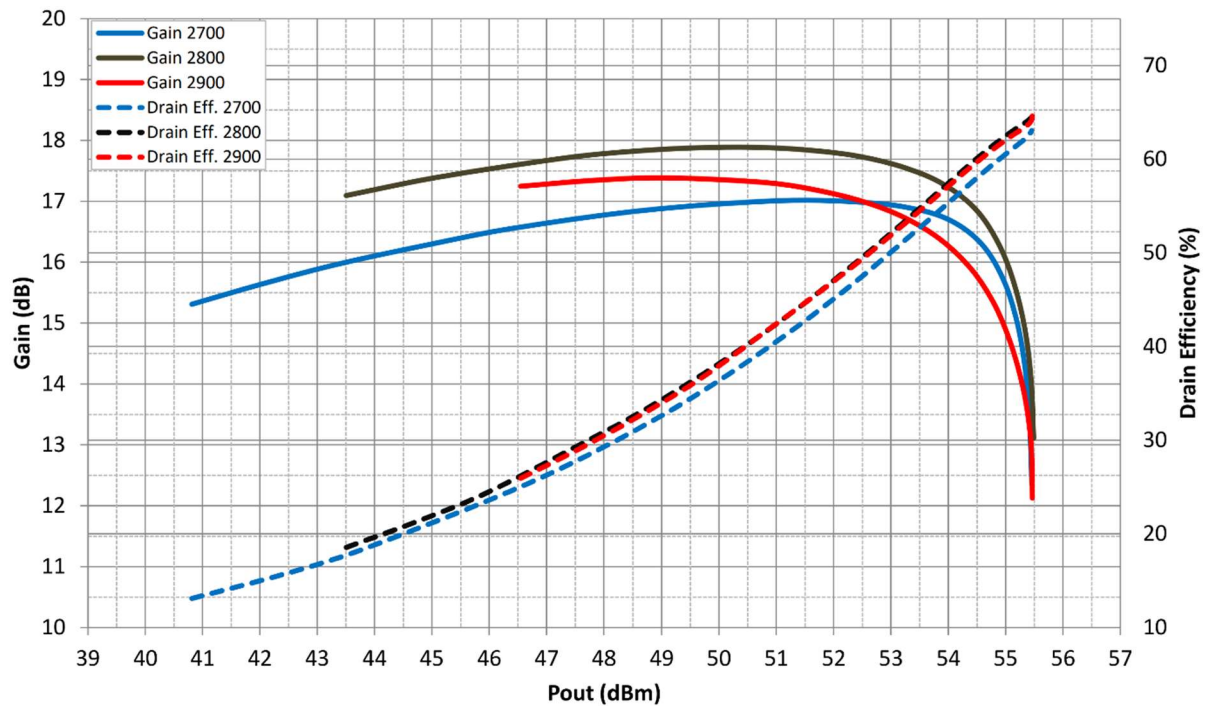
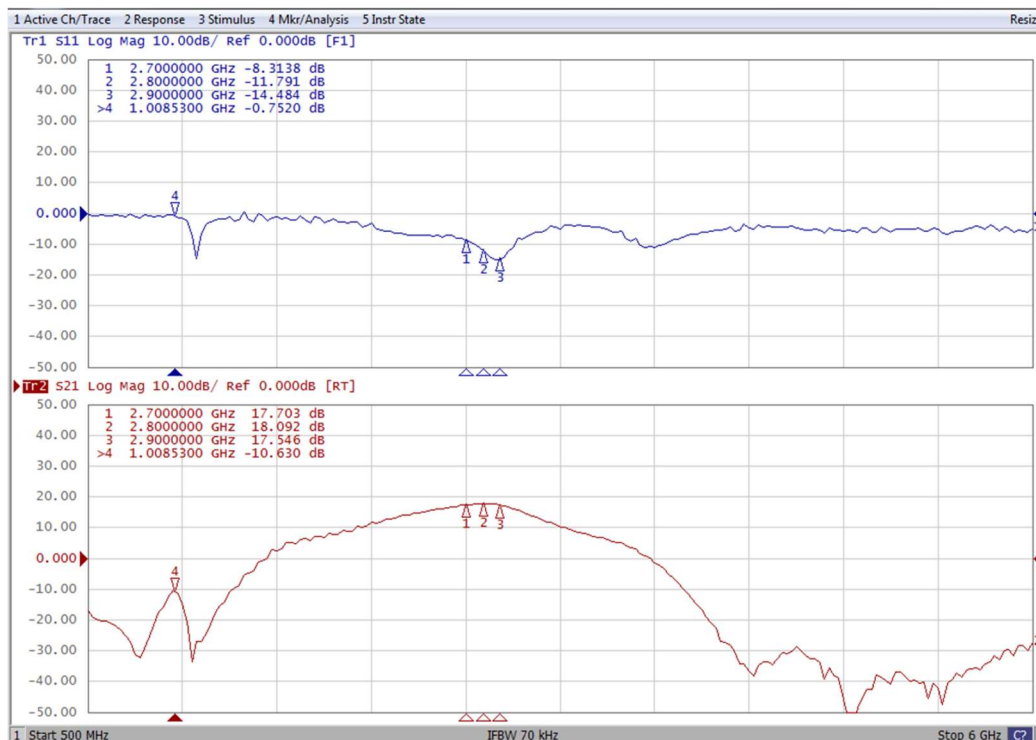
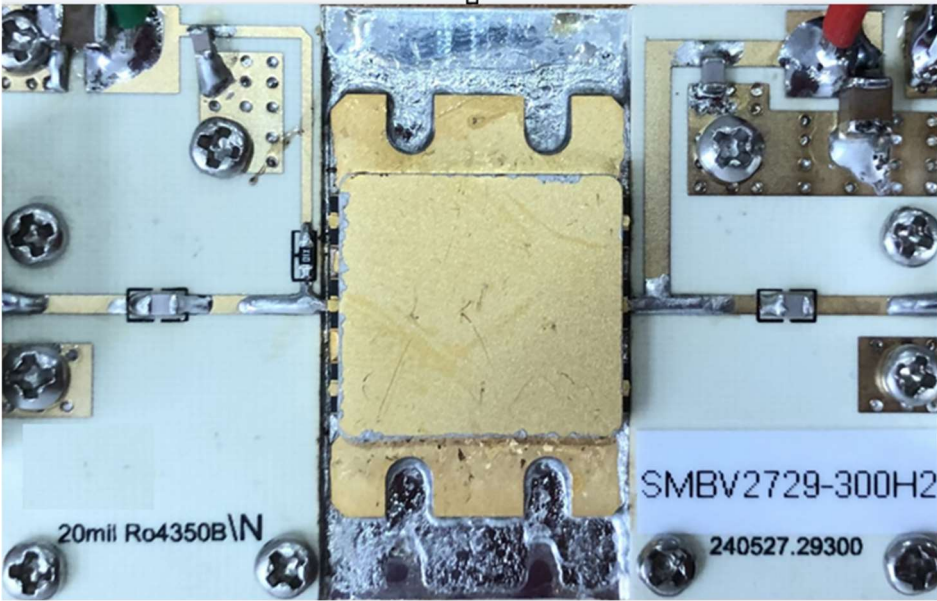
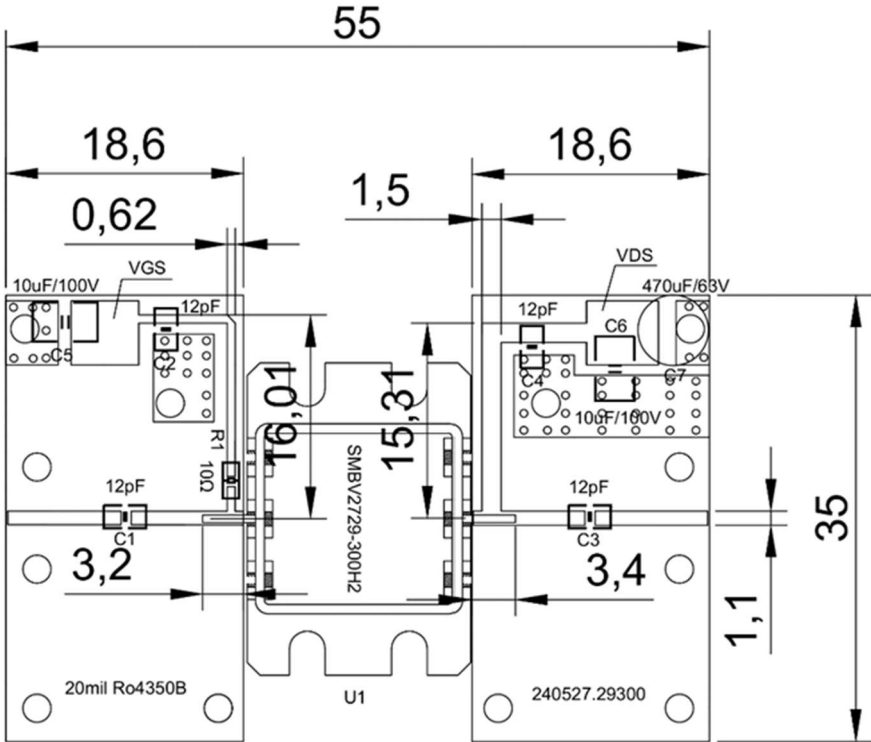


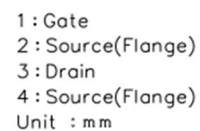
Figure 2. Network analyzer output S_{11}/S_{21} ($P_{in} = 0\text{dBm}$)



Reference Circuit of Test Fixture Assembly Diagram



Reference	Footprint	Value	Quantity
C1, C2, C3, C4	0805	12pF/250V	4
C5, C6	1210	10uF/100V	2
C7		470 uF/63V	1
R1	0603	10R	1
U1	H2	SMBV2729-300H2	1

**Table 6. Document revision history**

4 / 4